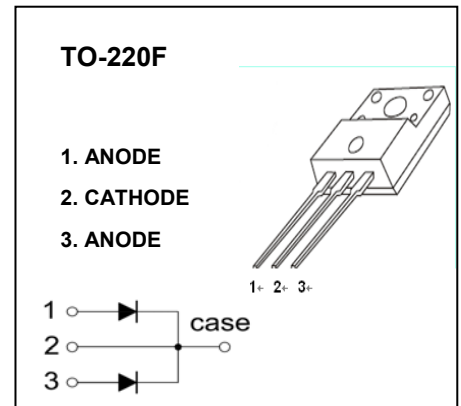


## TO-220F Plastic-Encapsulate Diodes

### MBR3060FCT SCHOTTKY BARRIER RECTIFIER

#### FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



#### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted )

Symbol	Parameter	Value	Unit
$V_{RRM}$	Peak repetitive reverse voltage	60	V
$V_{RWM}$	Working peak reverse voltage		
$V_R$	DC blocking voltage		
$V_{R(RMS)}$	RMS reverse voltage	42	V
$I_O$	Average rectified output current	30	A
$I_{FSM}$	Non-Repetitive peak forward surge current 8.3ms half sine wave	200	A
$P_D$	Power dissipation	2	W
$R_{\theta JA}$	Thermal resistance from junction to ambient	50	$^\circ\text{C}/\text{W}$
$T_j$	Junction temperature	125	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-55~+150	$^\circ\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified )

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=1\text{mA}$	60			V
Reverse current	$I_R$	$V_R=60\text{V}$			0.2	mA
Forward voltage	$V_{F1}$	$I_F=15\text{A}$			0.8	V
	$V_{F2}^*$	$I_F=30\text{A}$			0.95	V
Typical total capacitance	$C_{tot}^*$	$V_R=4\text{V}, f=1\text{MHz}$		400		pF

\*Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .